Advanced Power MOSFET

IRLZ34A

FEATURES

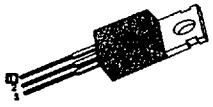
- Logic-Level Gate Drive
- Avalanche Rugged Technology
- Rugged Gate Oxide Technology
- Lower Input Capacitance
- Improved Gate Charge
- Extended Safe Operating Area
- Lower Leakage Current : 10 μA (Max.) @ V_{DS} = 60V
- Lower $R_{DS(ON)}$: 0.033 Ω (Typ.)

BV_{DSS} = 60 V

$R_{DS(on)}$ = 0.046 Ω

I_D = 30 A

TO-220



1.Gate 2. Drain 3. Source

Absolute Maximum Ratings

Symbol	Characteristic	Value	Units
V_{DSS}	Drain-to-Source Voltage	60	V
I_D	Continuous Drain Current (T_C=25°C)	30	A
	Continuous Drain Current (T_C=100°C)	21	
I_{DM}	Drain Current-Pulsed ①	105	A
V_{GS}	Gate-to-Source Voltage	±20	V
E_{AS}	Single Pulsed Avalanche Energy ②	463	mJ
I_{AR}	Avalanche Current ①	30	A
E_{AR}	Repetitive Avalanche Energy ①	8.3	mJ
dv/dt	Peak Diode Recovery dv/dt ③	5.5	V/ns
P_D	Total Power Dissipation (T_C=25°C)	83	W
	Linear Derating Factor	0.55	W/°C
T_J , T_{STG}	Operating Junction and Storage Temperature Range	- 55 to +175	°C
T_L	Maximum Lead Temp. for Soldering Purposes, 1/8" from case for 5-seconds	300	

Thermal Resistance

Symbol	Characteristic	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	--	1.81	°C/W
$R_{\theta CS}$	Case-to-Sink	0.5	--	
$R_{\theta JA}$	Junction-to-Ambient	--	62.5	

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Electrical Characteristics (T_C=25°C unless otherwise specified)

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
BV_{DSS}	Drain-Source Breakdown Voltage	60	--	--	V	V_{GS}=0V,I_D=250 μA
$\Delta BV/\Delta T_J$	Breakdown Voltage Temp. Coeff.	--	0.06	--	V/°C	I_D=250 μA *See Fig 7*
$V_{GS(th)}$	Gate Threshold Voltage	1.0	--	2.0	V	V_{DS}=5V,I_D=250 μA
I_{GSS}	Gate-Source Leakage , Forward	--	--	100	nA	V_{GS}=20V
	Gate-Source Leakage , Reverse	--	--	-100		V_{GS}=-20V
I_{DSS}	Drain-to-Source Leakage Current	--	--	10	μA	V_{DS}=60V
		--	--	100		V_{DS}=48V,T_C=150°C
$R_{DS(on)}$	Static Drain-Source On-State Resistance	--	--	0.046	Ω	V_{GS}=5V,I_D=15A ④
g_{fs}	Forward Transconductance	--	19	--	℧	V_{DS}=30V,I_D=15A ④
C_{iss}	Input Capacitance	--	970	1260	pF	V_{GS}=0V,V_{DS}=25V,f =1MHz *See Fig 5*
C_{oss}	Output Capacitance	--	334	385		
C_{rss}	Reverse Transfer Capacitance	--	131	150		
$t_{d(on)}$	Turn-On Delay Time	--	13	35	ns	V_{DD}=30V,I_D=30A, R_G=6 Ω *See Fig 13* ④⑤
t_r	Rise Time	--	21	55		
$t_{d(off)}$	Turn-Off Delay Time	--	36	80		
t_f	Fall Time	--	28	65		
Q_g	Total Gate Charge	--	27	35	nC	V_{DS}=48V,V_{GS}=5V, I_D=30A *See Fig 6 & Fig 12* ④⑤
Q_{gs}	Gate-Source Charge	--	9	--		
Q_{gd}	Gate-Drain("Miller") Charge	--	12	--		

Source-Drain Diode Ratings and Characteristics

Symbol	Characteristic	Min.	Typ.	Max.	Units	Test Condition
I_S	Continuous Source Current	--	--	30	A	Integral reverse pn-diode in the MOSFET
I_{SM}	Pulsed-Source Current ①	--	--	105		
V_{SD}	Diode Forward Voltage ④	--	--	1.6	V	T_J=25°C,I_S=30A,V_{GS}=0V
t_{rr}	Reverse Recovery Time	--	64	--	ns	T_J=25°C,I_F=30A
Q_{rr}	Reverse Recovery Charge	--	0.122	--	μC	di_F/dt=100A/μs ④

Notes ;

① Repetitive Rating : Pulse Width Limited by Maximum Junction Temperature

② L=0.6mH, I_{AS}=30A, V_{DD}=25V, R_G=27Ω, Starting T_J=25°C

③ I_{SD} ≤30A, di/dt ≤300A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J=25°C

④ Pulse Test : Pulse Width = 250 μs, Duty Cycle ≤ 2%

⑤ Essentially Independent of Operating Temperature

Fig 1. Output Characteristics

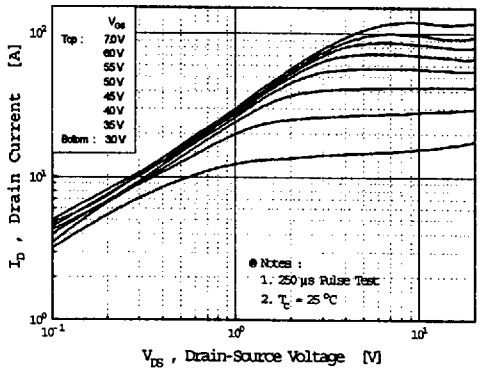


Fig 2. Transfer Characteristics

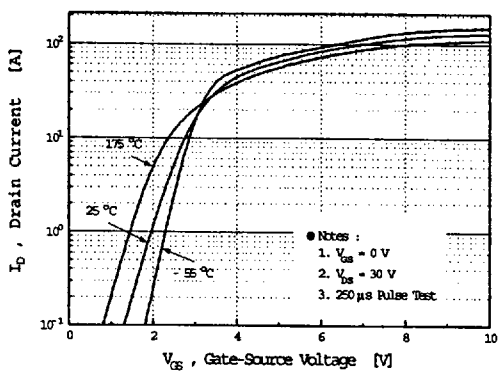


Fig 3. On-Resistance vs. Drain Current

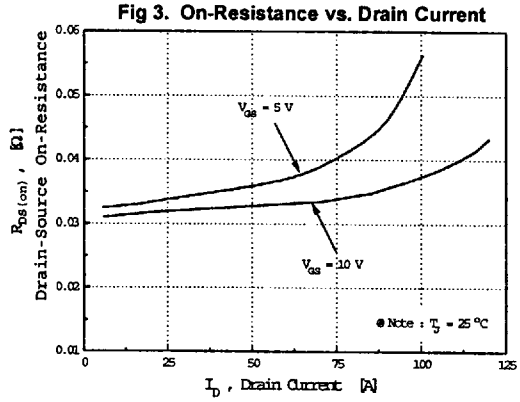


Fig 4. Source-Drain Diode Forward Voltage

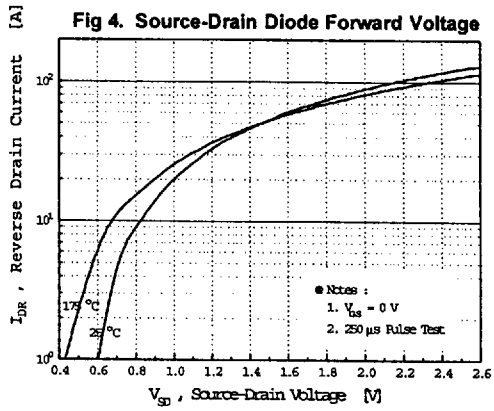


Fig 5. Capacitance vs. Drain-Source Voltage

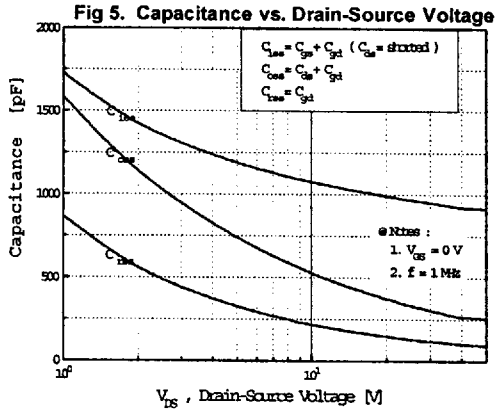


Fig 6. Gate Charge vs. Gate-Source Voltage

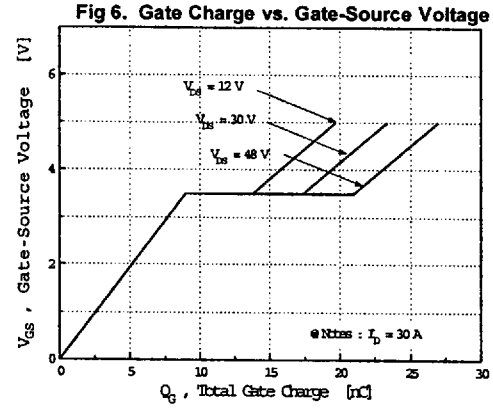


Fig 7. Breakdown Voltage vs. Temperature

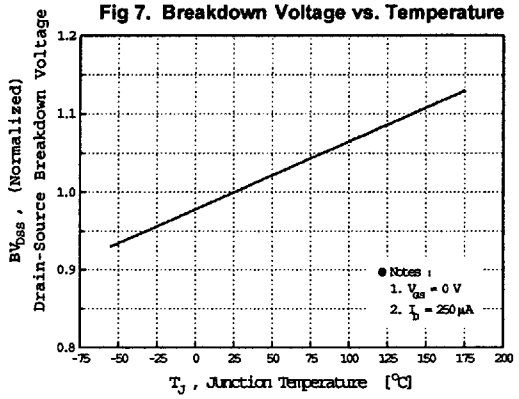


Fig 8. On-Resistance vs. Temperature

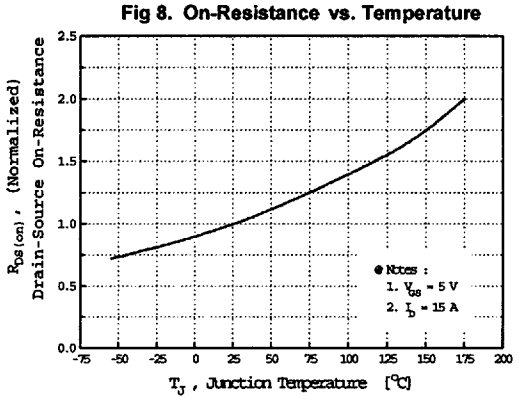


Fig 9. Max. Safe Operating Area

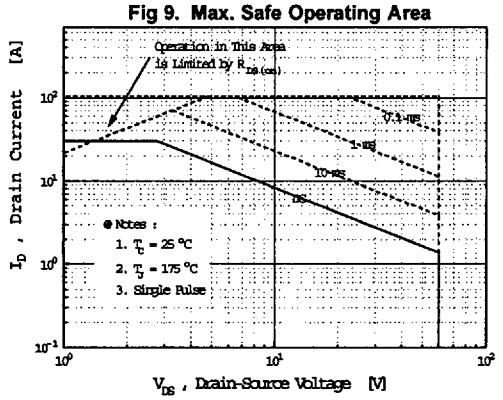


Fig 10. Max. Drain Current vs. Case Temperature

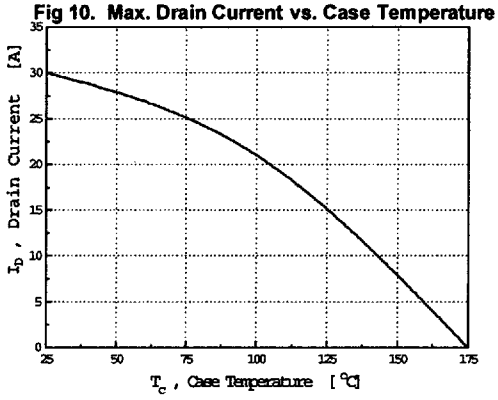


Fig 11. Thermal Response

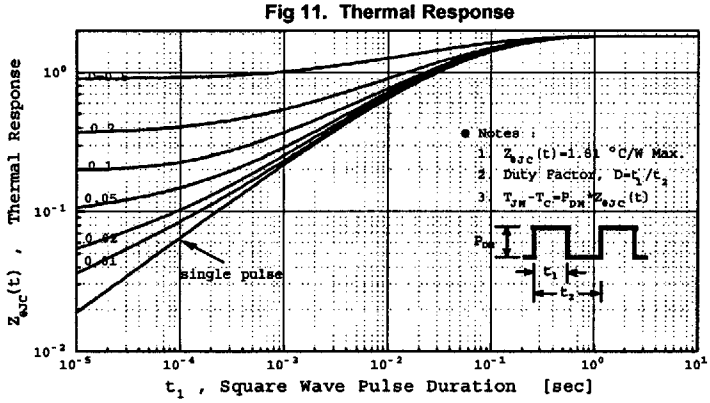


Fig 12. Gate Charge Test Circuit & Waveform

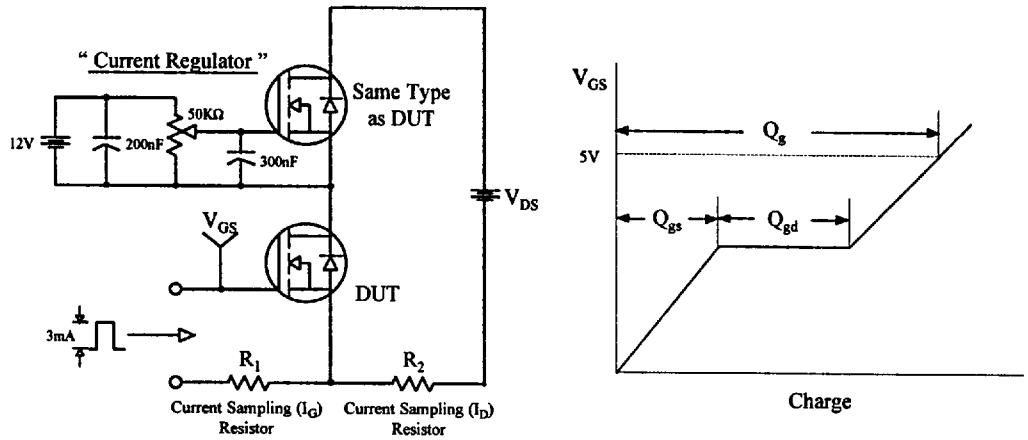


Fig 13. Resistive Switching Test Circuit & Waveforms

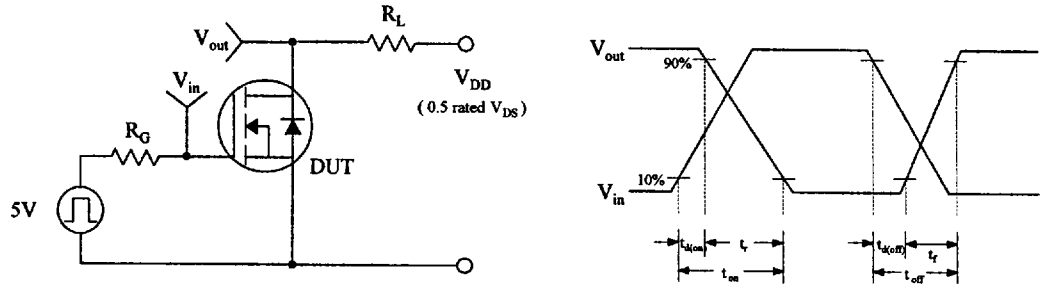


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms

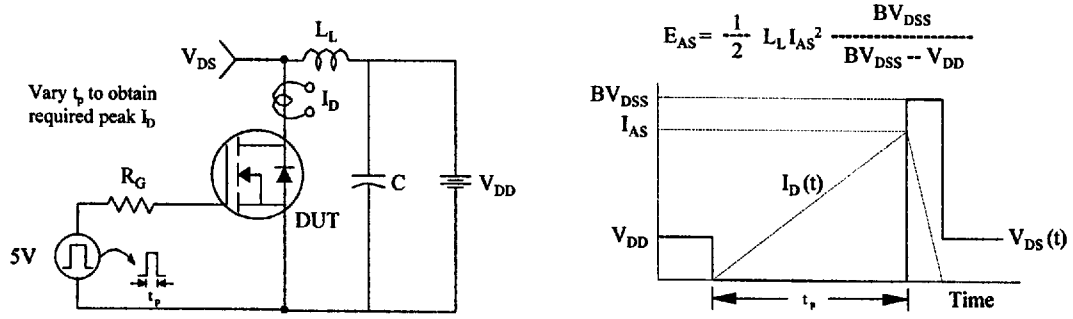
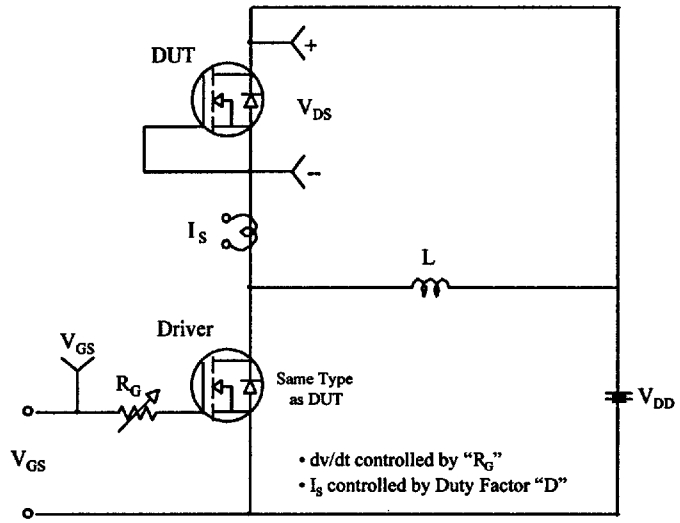
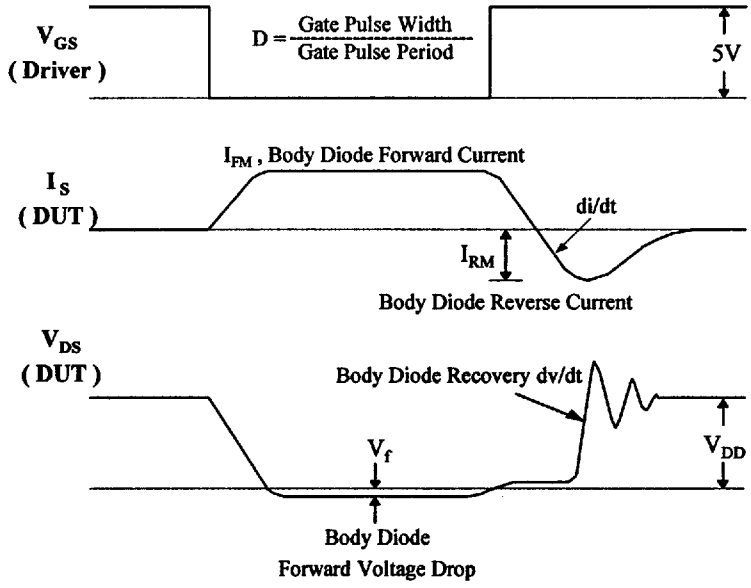
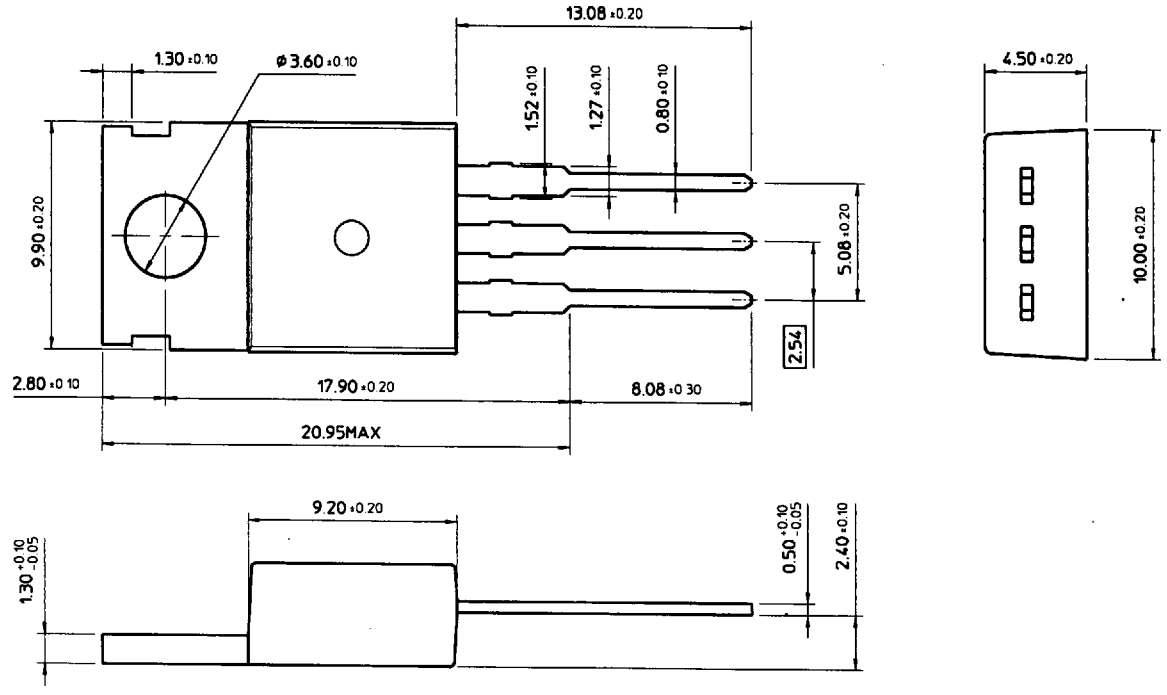


Fig 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms





TO-220 (1)



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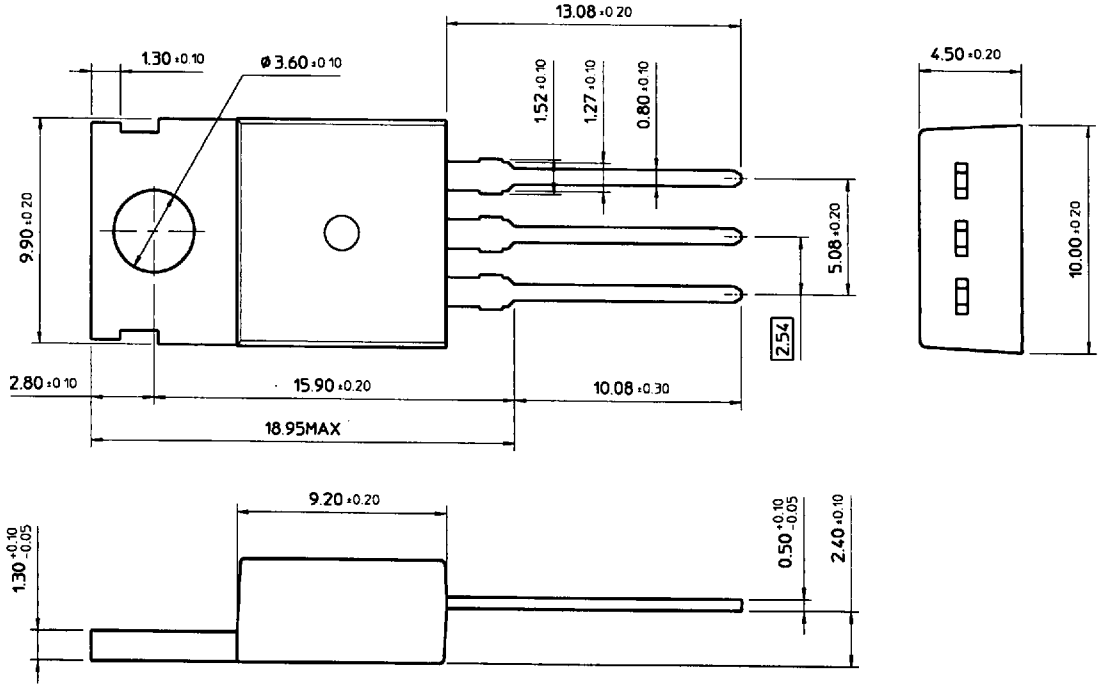

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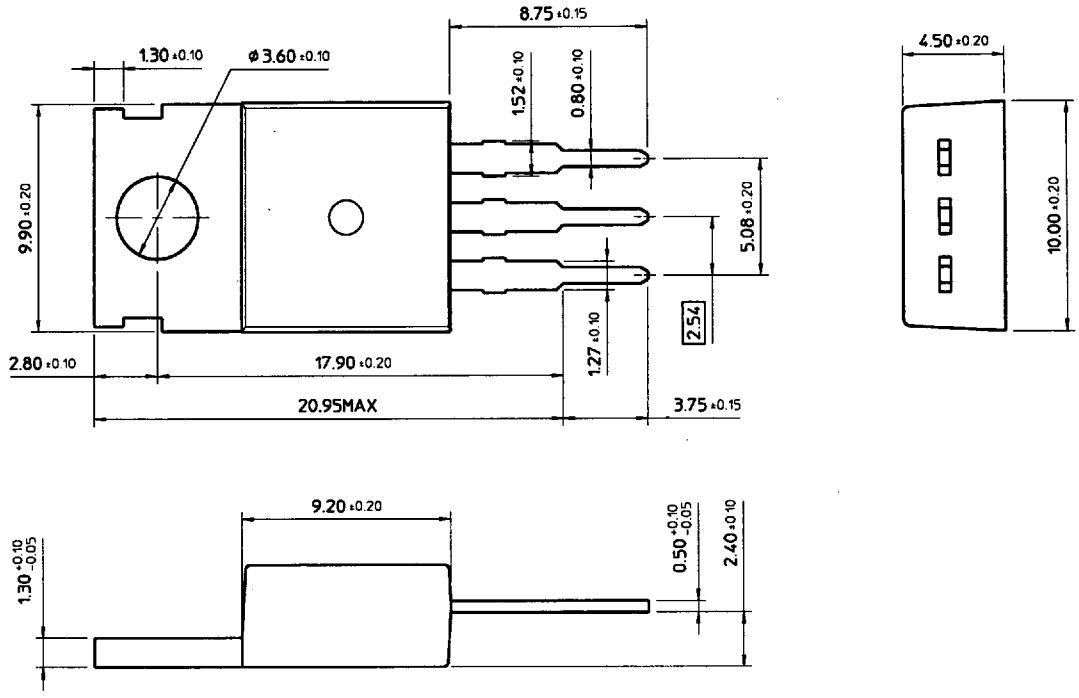

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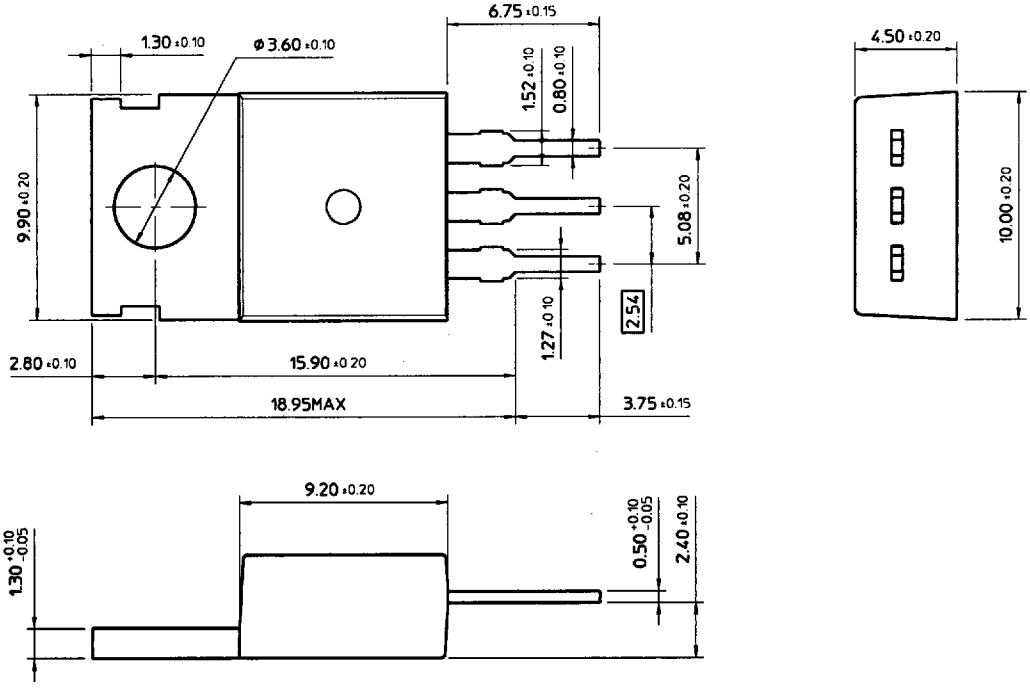

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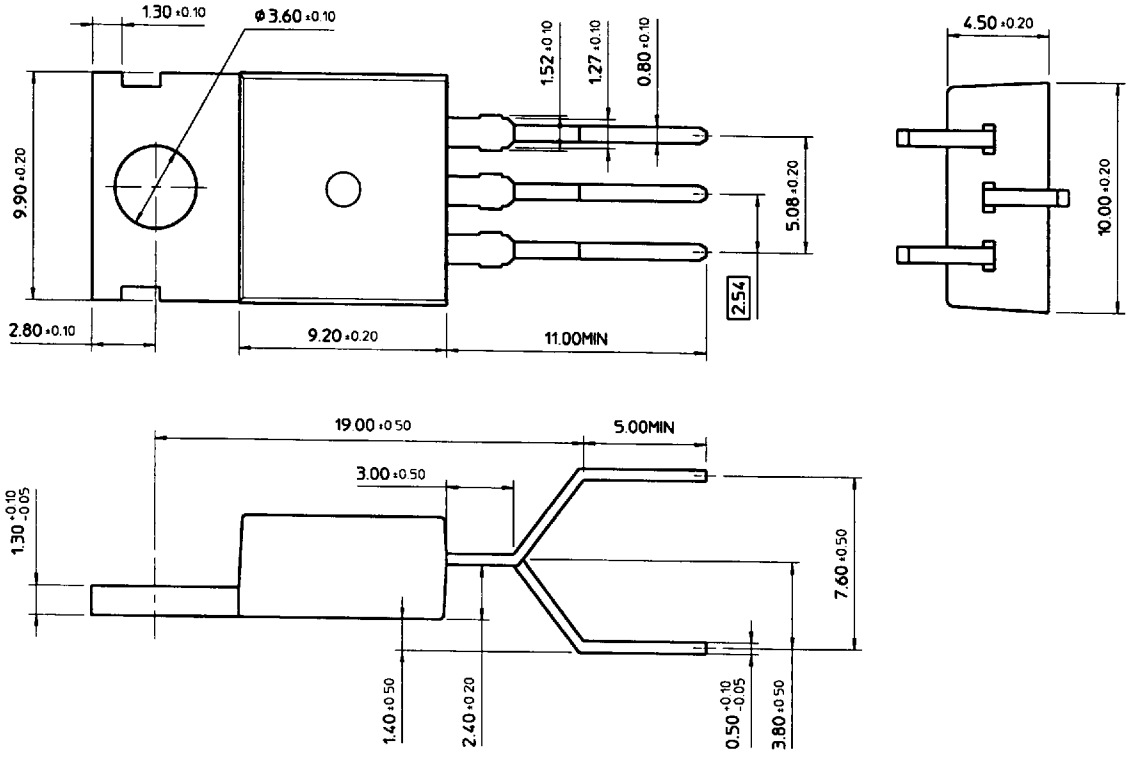
TO-220 (5)


1.30 ±0.10
φ3.60 ±0.10
1.52 ±0.10
1.27 ±0.10
0.80 ±0.10
4.50 ±0.20
9.90 ±0.20
5.08 ±0.20
10.00 ±0.20
2.54
2.80 ±0.10
9.20 ±0.20
11.00MIN
19.00 ±0.50
5.00MIN
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1.30 +0.10 -0.05
7.60 ±0.50
1.40 ±0.50
2.40 ±0.20
0.50 +0.10 -0.05
3.80 ±0.50

NOTE